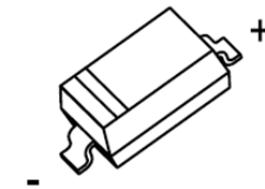


## FEATURES

- High breakdown voltage
- Low turn-on voltage
- Guard ring construction for transient protection



## MARKING: S9



**SOD-123**

## Maximum Ratings @ $T_a=25^\circ\text{C}$

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	$V_{RRM}$	100	V
Working peak reverse voltage	$V_{RWM}$		
Forward continuous current	$I_F$	150	mA
Repetitive peak forward current (Note 1) @ $t_p < 1.0\text{s}$ , Duty Cycle < 50%	$I_{FRM}$	350	mA
Non-repetitive Peak Forward surge current @ $t = 8.3\text{ms}$	$I_{FSM}$	750	mA
Power dissipation	$P_D$	500	mW
Thermal resistance junction to ambient air	$R_{\theta JA}$	200	°C/W
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{STG}$	-55~+150	°C

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

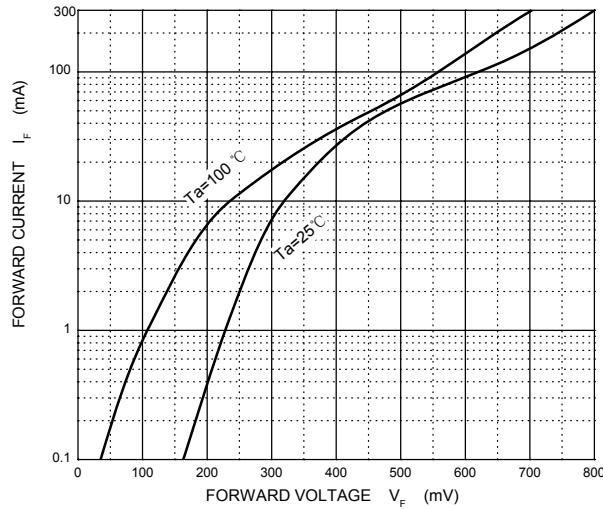
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage (Note 2)	$V_R$	$I_R=100\mu\text{A}$	100			V
Reverse voltage leakage current	$I_R$	$V_{R1}=1.5\text{V}$			0.3	μA
		$V_{R2}=10\text{V}$			0.5	
		$V_{R3}=50\text{V}$			1	
		$V_{R4}=75\text{V}$			2	
Forward voltage (Note 2)	$V_F$	$I_{F1}=0.1\text{mA}$			0.25	V
		$I_{F2}=10\text{mA}$			0.45	
		$I_{F3}=250\text{mA}$			1	
Diode capacitance	$C_T$	$V_R=0, f=1\text{MHz}$		20		pF
		$V_R=1\text{V}, f=1\text{MHz}$		12		

Notes: 1. Part mounted on FR-4 board with recommended pad layout.

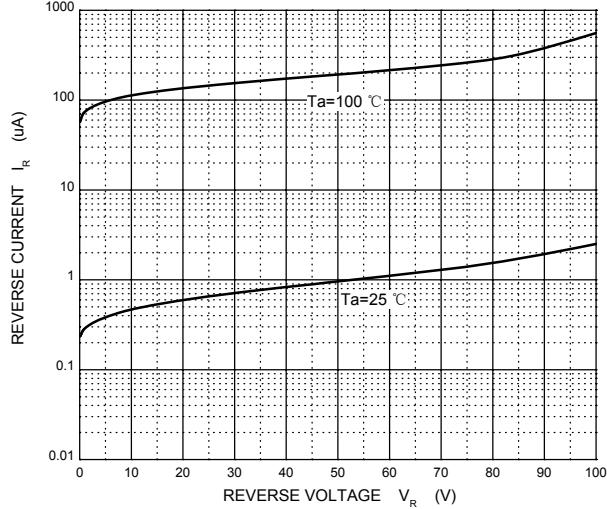
2. Short duration pulse test used to minimize self-heating effect.

### Typical Characteristics

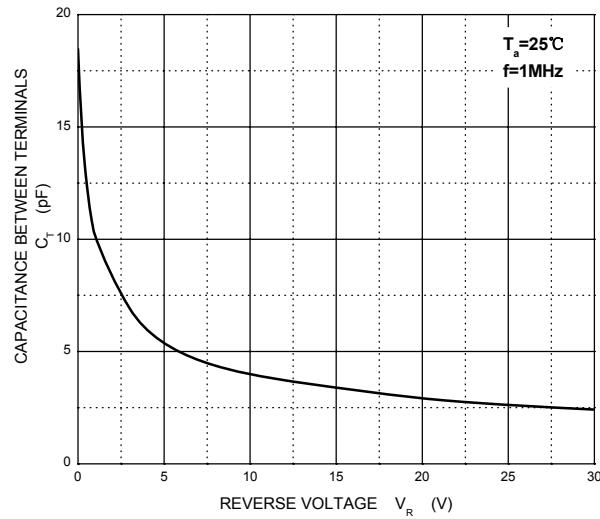
**Forward Characteristics**



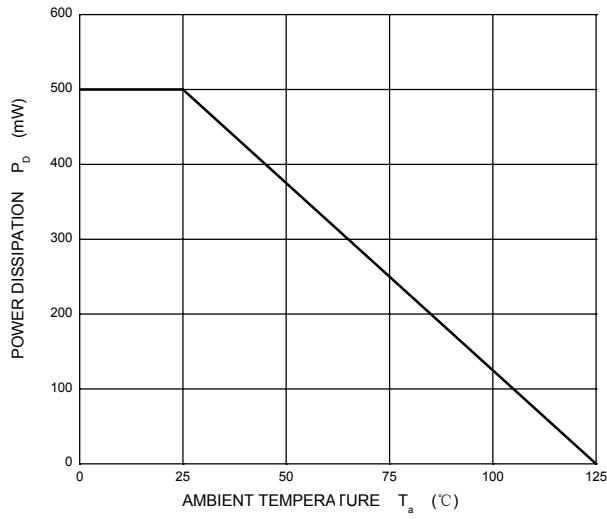
**Reverse Characteristics**



**Capacitance Characteristics**

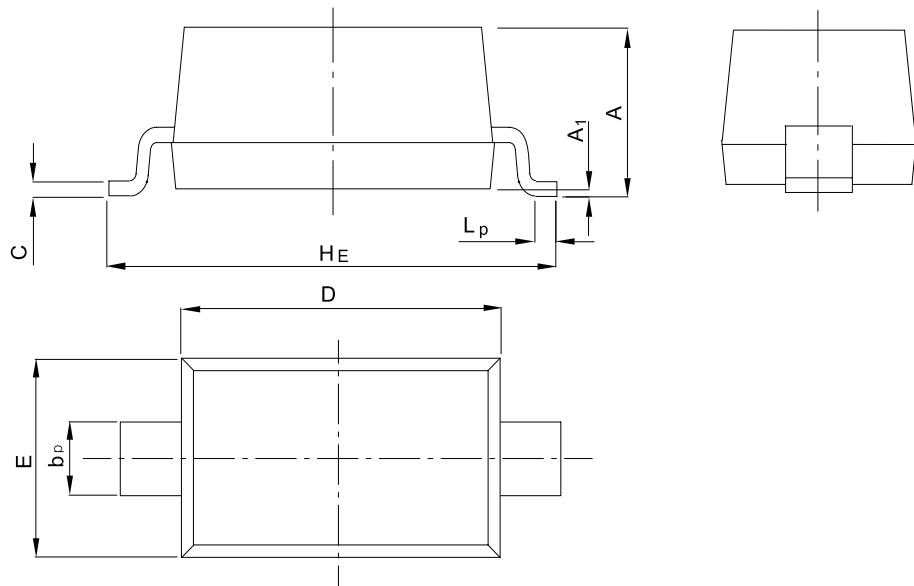


**Power Derating Curve**



**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-123**

UNIT	A	b <sub>P</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>P</sub>
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20